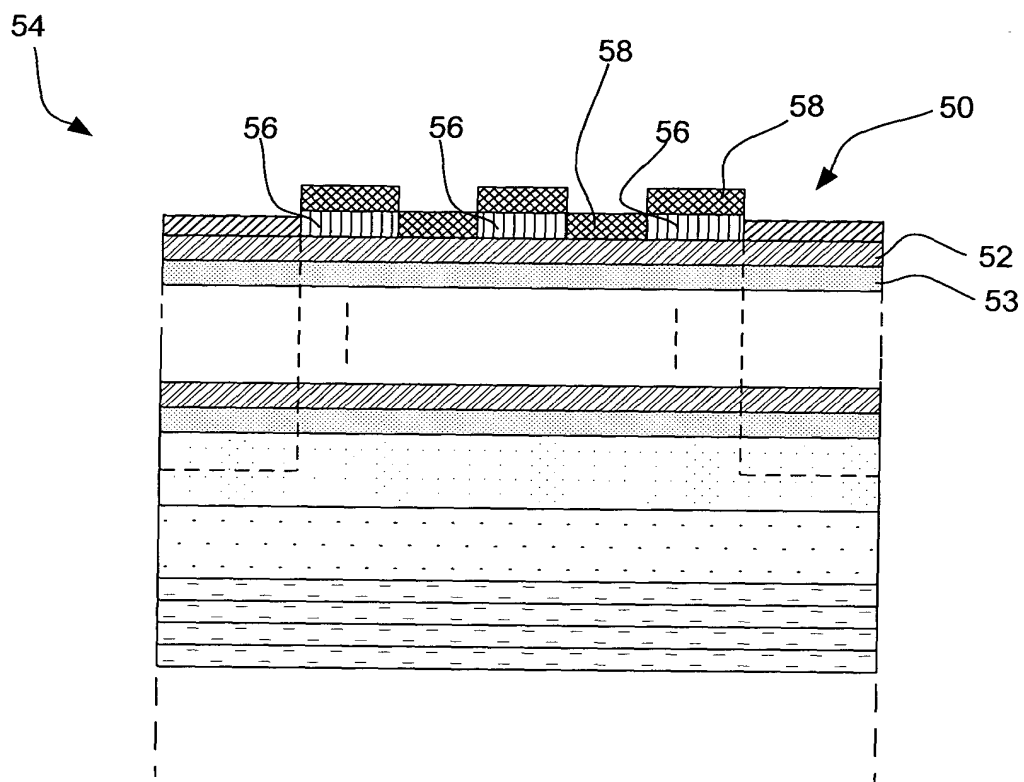
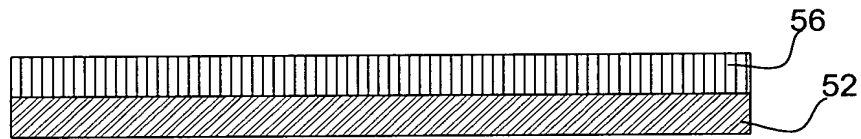


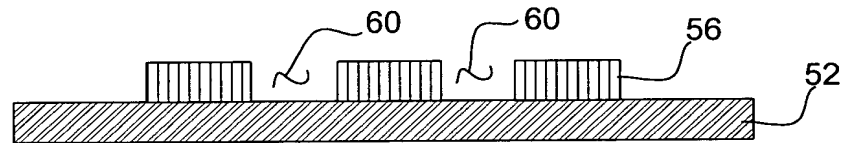
**FIG. 1**



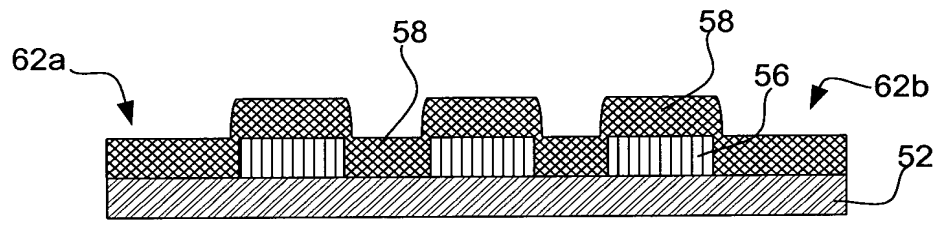
**FIG. 2**



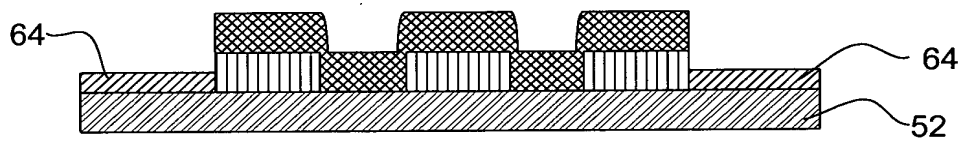
**FIG. 3A**



**FIG. 3B**

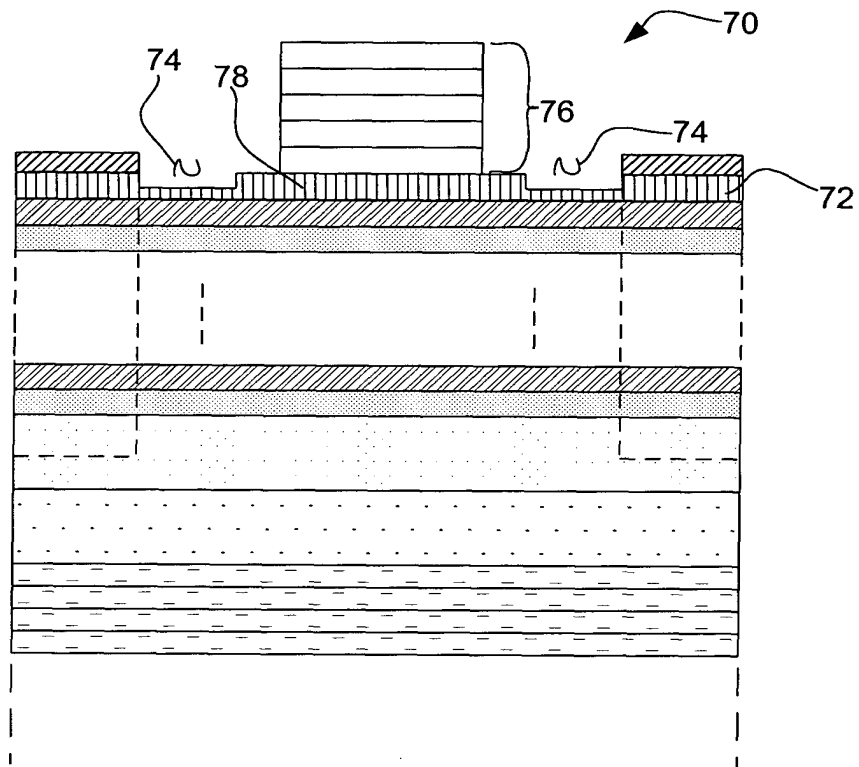


**FIG. 3C**

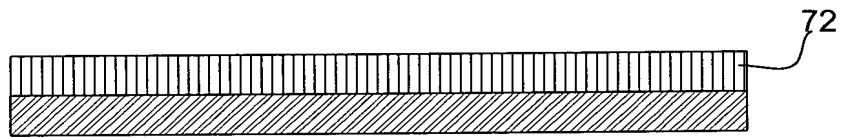


**FIG. 3D**

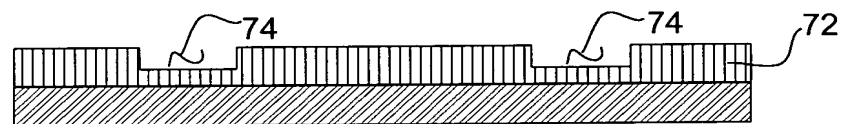
FIG. 4 is a cross-sectional view of a semiconductor device 70, showing a substrate 72 with a top layer 74. A central region 76 is defined by a top layer 74 and a bottom layer 78. The central region 76 is filled with a material having a different pattern than the surrounding layers. The device 70 is shown in a cross-sectional view, with the central region 76 being the main feature of interest.



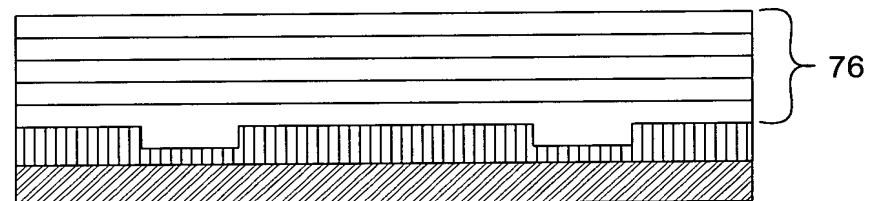
**FIG. 4**



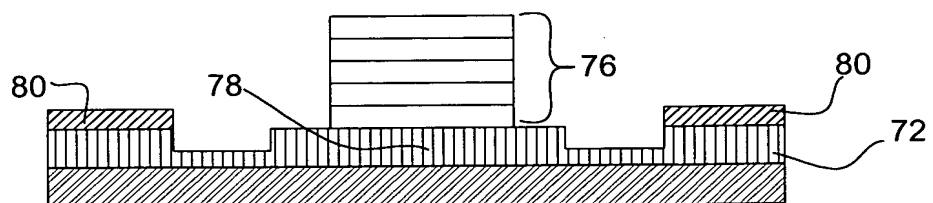
**FIG. 5A**



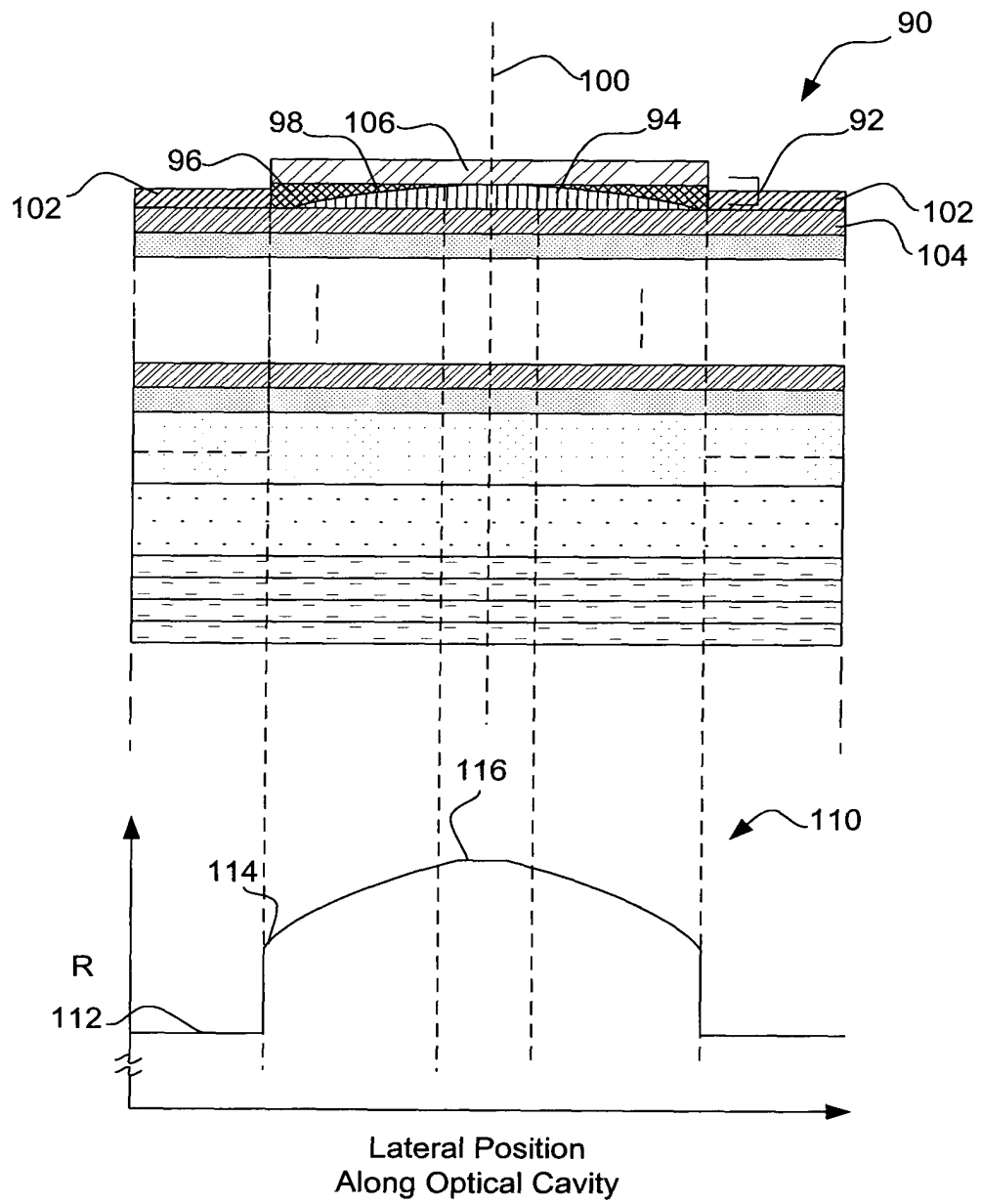
**FIG. 5B**



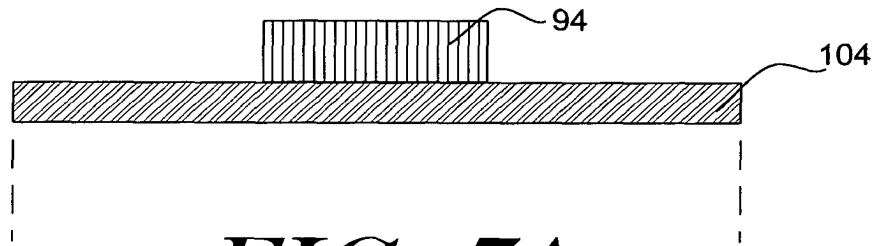
**FIG. 5C**



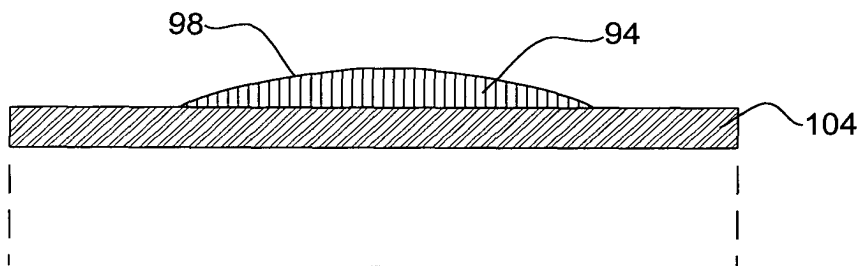
**FIG. 5D**



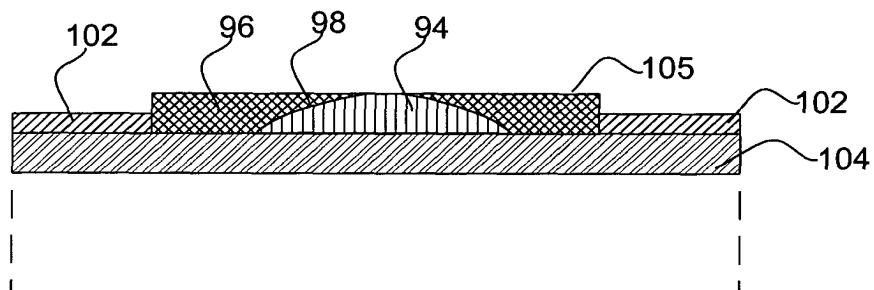
**FIG. 6**



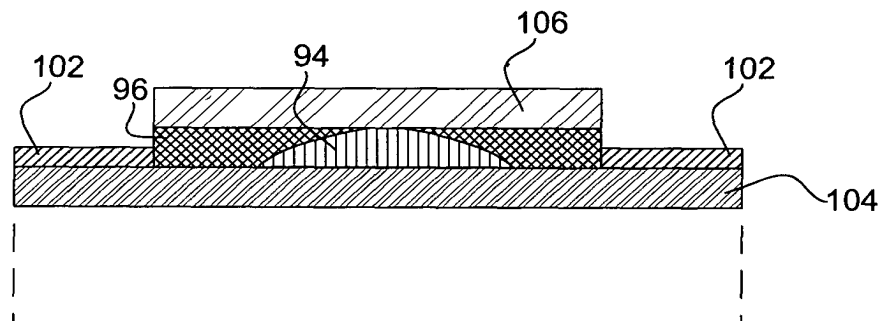
**FIG. 7A**



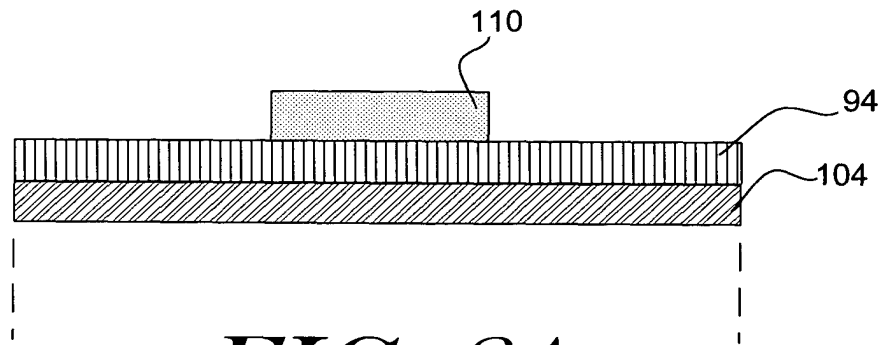
**FIG. 7B**



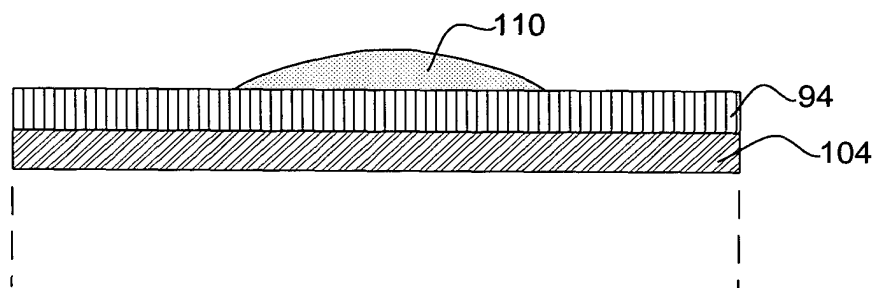
**FIG. 7C**



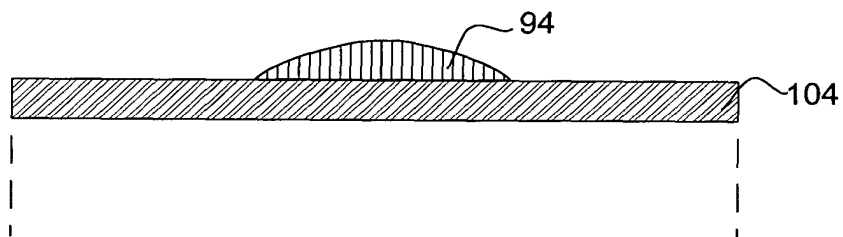
**FIG. 7D**



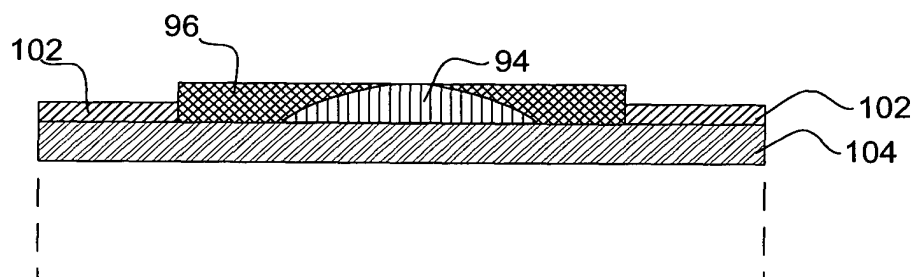
**FIG. 8A**



**FIG. 8B**

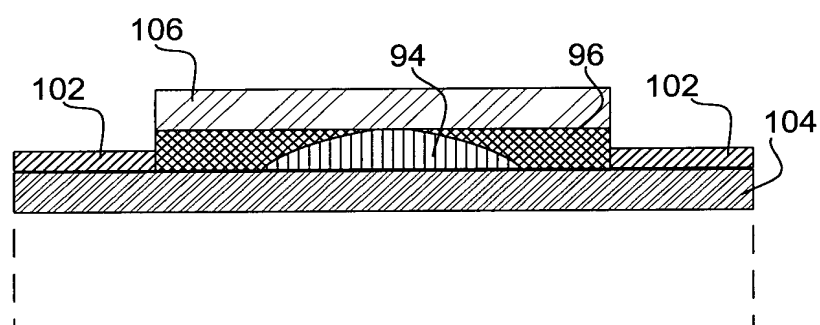


**FIG. 8C**

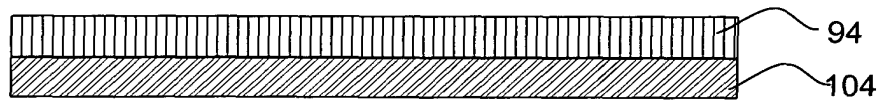


**FIG. 8D**

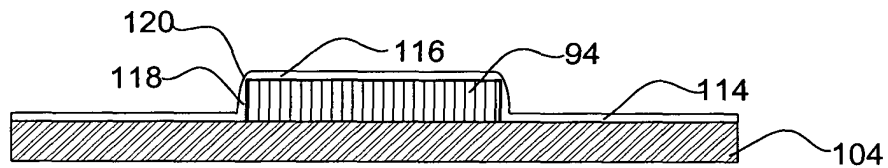




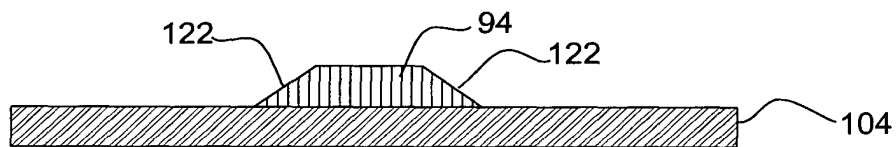
*FIG. 8E*



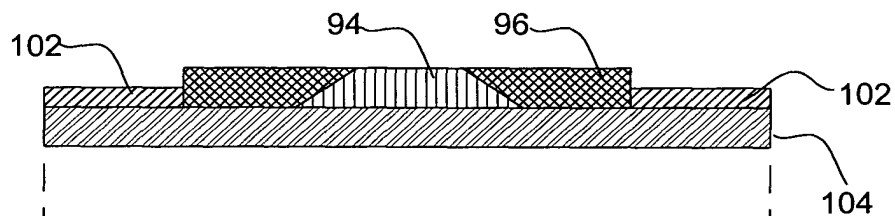
**FIG. 9A**



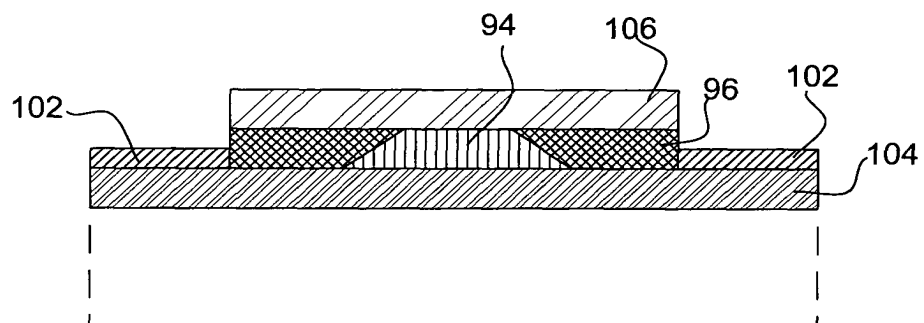
**FIG. 9B**



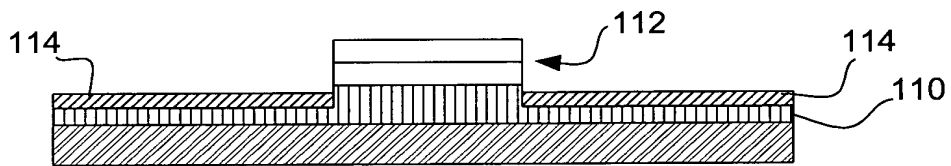
**FIG. 9C**



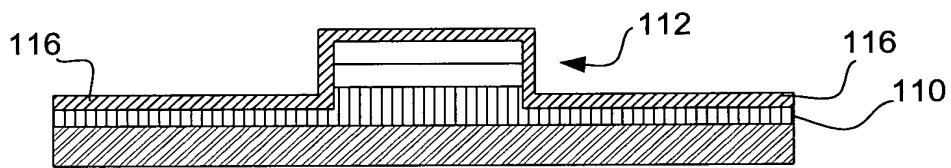
**FIG. 9D**



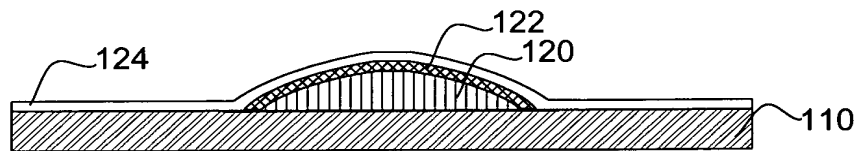
***FIG. 9E***



**FIG. 10**



**FIG. 11**



**FIG. 12**